## NSN 5961-01-351-1947

Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-351-1947 **Inclosure Material:** Ceramic **Overall Length:** 1.000 inches **Overall Height:** Between 0.030 inches and 0.115 inches Overall Width: 0.300 inches **Component Name And Quantity:** 4 transistor **Mounting Method: Terminal Semiconductor Material:** Silicon all transistor Voltage Rating In Volts Per Characteristic: 75.0 collector to base voltage/static/emitter open all transistor and 50.0 collector to emitter voltage/static/base open all transistor and 6.0 emitter to base voltage, static, collector open all transistor **Current Rating Per Characteristic:** 800.00 milliamperes source cutoff current all transistor **Power Rating Per Characteristic:** 0.4 watts small-signal input power, common-collector preset all transistor **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius ambient air **Special Features:** All transistor junction pattern arrangement: npn **Test Data Document:** 81349-mil-prf-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 14 pin **Specification Data:** 81349-mil-prf-19500/559 government specification Shelf Life: N/a **Unit Of Measure: Demilitarization:** Yes - demil/mli

Mil-std (military Standard): Mil-prf-19500 spec.

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